AMENDMENTS TO THE CLAIMS

Claims 1-10 (Canceled)

Claim 11 (Original): A method comprising selectively etching a trench dielectric layer and a contact dielectric layer in a structure comprising the trench dielectric layer, the contact dielectric layer, and an etch stop layer therebetween comprising undoped silicon oxide and having a hole therein, the hole containing a trench dielectric layer material, with an etch gas including $C_2H_2F_4$.

Claim 12 (Withdrawn): A method of forming an interconnect structure, the method comprising

depositing an etch stop layer, containing an undoped silicon oxide, on a contact dielectric layer containing a first oxide comprising silicon;

forming a hole through the etch stop layer;

depositing a trench dielectric layer, containing a second oxide comprising silicon, on the etch stop layer and in the hole through the etch stop layer;

forming a trench in the trench dielectric layer and a hole through the contact dielectric layer by etching the first and second oxides; and

depositing an electrically conductive interconnect in the trench, the hole through the etch stop layer and the hole through the contact dielectric layer, wherein

forming the trench comprises etching the second oxide with a chemistry containing $C_2H_2F_4$.

Claim 13 (Canceled)

Claim 14 (Withdrawn): The method according to Claim 12, wherein forming the hole through the etch stop layer comprises etching with a chemistry containing at least one of C_xF_y (where x = 1-6, and y = (2x-2), 2x or (2x+2), but is at least 4) and $C_aH_bF_c$ (where a = 1 or 2, b = 0-2, and c = (2a+2-b)).

Claims 15-17 (Canceled)

Claim 18 (New): The method according to Claim 11, wherein the method further comprises partially etching the contact dielectric layer before the trench dielectric layer is etched.